



74LVC2G00

Description

The 74LVC2G00 is a dual, two input NAND gate. Both gates have push-pull outputs designed for operation over a power supply range of 1.65V to 5.5V. The device is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing damaging current backflow when the device is powered down. Each gate performs the positive Boolean function:

$$Y = \overline{A \bullet B} \ {\rm or} \ Y = \overline{A} + \overline{B}$$

DUAL 2-INPUT NAND GATE

Pin Assignments



Features

- Wide Supply Voltage Range from 1.65 to 5.5V
- ± 24mA Output Drive at 3.3V
- CMOS Low Power Consumption
- IOFF Supports Partial-Power-Down Mode Operation
- Inputs accept up to 5.5V
- Schmitt Trigger Action at all inputs makes the circuit tolerant for slower input rise and fall times. The hysteresis is typically 100mV at V_{CC} = 3.0V.
- ESD Protection Exceeds JESD 22
 - 2000-V Human Body Model (A114)
 - Exceeds 1000-V Charged Device Model (C101)
- Latch-Up Exceeds 100mA per JESD 78, Class I
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Applications

- Voltage Level Shifting
- General Purpose Logic
- Power Down Signal Isolation
- Wide Array of Products Such as:
 - PCs, Networking, Notebooks, Netbooks, PDAs
 - Tablet Computers, E-readers
 - Computer Peripherals, Hard Drives, CD/DVD ROMs
 - TVs, DVDs, DVRs, Set Top Boxes
 - Cell Phones, Personal Navigation / GPS
 - MP3 Players, Cameras, Video Recorders

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Ordering Information (Note 4)



	Package	Package	Package	7" Tape and Reel (Note 6)		
Device	Code	(Note 5)	Size	Quantity	Part Number Suffix	
74LVC2G00HD4-7	HD4	X2-DFN2010-8	1.95mm x 1.0mm x 0.4mm 0.5 mm lead pitch	5,000/Tape & Reel	-7	
74LVC2G00HK3-7	НКЗ	X2-DFN1410-8	1.35mm x 1.0mm x 0.35mm 0.4 mm lead pitch	5,000/Tape & Reel	-7	
74LVC2G00RA3-7	RA3	X2-DFN1210-8	1.2mm x 1.0mm x 0.35mm 0.3 mm lead pitch	5,000/Tape & Reel	-7	

Notes: 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

5. Pad layout as shown in Diodes Incorporated's package outline PDFs, which can be found on our website at http://www.diodes.com/packageoutlines.html.

6. The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf.

Pin Descriptions

Pin Name	Pin No.	Description
1A	1	Data Input
1B	2	Data Input
2Y	3	Data Output
GND	4	Ground
2A	5	Data Input
2B	6	Data Input
1Y	7	Data Output
Vcc	8	Supply Voltage

Logic Diagram



Function Table

Inp	Output	
Α	В	Y
L	L	Н
L	н	Н
Н	L	Н
Н	н	L



Absolute Maximum Ratings (Notes 7 & 8)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
Vcc	Supply Voltage	-0.5 to +6.5	V
VI	Input Voltage	-0.5 to +6.5	V
Vo	Output Voltage -Active Mode	-0.5 to V _{CC} +0.5	V
VO	Output Voltage Power Down Mode	-0.5 to +6.5	V
I _{IK}	Input Clamp Current VI<0	-50	mA
Ι _{ΟΚ}	Output Clamp Current (Vo < 0 OR Vo > Vcc)	±50	mA
lo	Continuous Output Current (Vo = 0 to V _{CC})	±50	mA
Icc	Continuous Current Through V _{CC}	100	mA
I _{GND}	Continuous Current Through GND	-100	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Notes: 7. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device

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Recommended Operating Conditions (Note 9)

Symbol	Р	arameter	Min	Мах	Unit
		Operating	1.65	5.5	
Vcc	V _{CC} Operating Voltage	Data Retention Only	1.5	_	V
VI	Input Voltage		0	5.5	V
N/	Output Voltage Active Mode		0	V _{CC}	V
Vo	Output Voltage Power-Down Mode		0	5.5	V
		$V_{CC} = 1.65V$	—	-4	
		$V_{CC} = 2.3V$	—	-8	
I _{OH}	High-Level Output Current	$V_{CC} = 2.7 V$	—	-12	mA
ЧОН	$V_{\rm CC} = 3.0 V$	$V_{aa} = 3.0V$	—	-16	IIIA
		VCC = 5.0 V		-24	
		$V_{CC} = 4.5V$	—	-32	
		V _{CC} = 1.65V	—	4	
		$V_{CC} = 2.3V$	—	8	
IOL	Low-Level Output Current	$V_{CC} = 2.7 V$	—	12	mA
IOL		V _{CC} = 3.0V	—	16	
		v _{CC} = 3.0v		24	
		$V_{CC} = 4.5V$		32	
Δt/ΔV	Input Transition Rise or Fall Rate	$V_{CC} = 1.65V$ to 2.7V	_	20	ns/V
		$V_{CC} = 2.7V$ to 5.5V	—	10	115/ V
TA	Operating F	ree-Air Temperature	-40	+125	°C

Note: 9. Unused inputs should be held at V_{CC} or Ground.



Electrical Characteristics (All typical values are at T_A = +25°C)

0	Demonst	To al Querditi		-40	°C to +8	5°C	-40°C to	+125°C	11
Symbol	Parameter	Test Conditions	Vcc	Min	Тур.	Max	Min	Max	Unit
			$V_{CC} = 1.65V$ to 1.95V	0.65 x V _{CC}		_	0.65 x V _{CC}	_	
	High-Level Input Voltage		V _{CC} = 2.3V to 2.7V	1.7		_	1.7	_	.,
VIH		_	$V_{CC} = 2.7 V \text{ to } 3.6 V$	2.0	_	_	2.0	_	V
			V _{CC} = 4.5V to 5.5V	0.7 x V _{CC}	_	_	0.7 x V _{CC}	_	
			$V_{CC} = 1.65V$ to 1.95V	_	_	0.35 x V _{CC}		0.35 x V _{CC}	
	Low-Level		$V_{CC} = 2.3V$ to 2.7V	_	_	0.7		0.7	v
VIL	Input Voltage	_	$V_{CC} = 2.7V$ to 3.6V	_		0.8		0.8	v
			$V_{CC} = 4.5V$ to 5.5V	—		0.3 x V _{CC}		0.3 x V _{CC}	
		I _{OH} = -100μA	1.65V to 5.5V	$V_{CC} - 0.1$	Vcc	_	V _{CC} – 0.1	_	
		I _{OH} = -4mA	1.65V	1.2	1.53	_	0.95	_	
	High-Level	I _{OH} = -8mA	2.3V	1.9	2.13	_	1.7	_	
Vон	Output	I _{OH} = -12mA	2.7	2.2	2.5	_	1.9	_	V
	Voltage I _{OH} = -16	I _{OH} = -16mA	2)/	2.4	2.7	_	2.2	_	
		I _{OH} = -24mA	3V	2.3	2.6	_	2.0	_	
		I _{OH} = -32mA	4.5V	3.8	4.1	_	3.4	_	
		I _{OL} = 100μA	1.65V to 5.5V	_	0	0.1		0.1	
		$I_{OL} = 4mA$	1.65V	_	0.08	0.45	_	0.7	
	Low-Level	$I_{OL} = 8mA$	2.3V	_	0.14	0.3	_	0.45	V
Vol	Output	$I_{OL} = 12mA$	2.7V	_	0.19	0.4	_	0.6	
	Voltage	I _{OL} = 16mA	3V	_	0.25	0.4	_	0.6	
		$I_{OL} = 24mA$	3V	—	0.37	0.55	_	0.8	
		$I_{OL} = 32mA$	4.5V	—	0.43	0.55		0.8	
I _I	Input Current	$V_1 = 5.5V$ or GND	0V to 5.5V	_	± 0.1	±5	_	± 20	μA
I _{OFF}	Power Down Leakage Current	V_1 or $V_0 = 5.5V$	0V	_	± 0.1	±10	_	±20	μA
I _{CC}	Supply Current	$V_1 = 5.5V$ or GND $I_0=0A$	1.65V to 5.5V	_	0.1	10	_	40	μA
ΔI _{CC}	Additional Supply Current	One input at $V_{CC} - 0.6V$ Other inputs at V_{CC} or GND	2.3V to 5.5V	_	5	500	_	5,000	μΑ
Cı	Input Capacitance	$V_{I} = V_{CC}$ or GND	3.3V	_	2.5	_	_	_	pF



Operating Characteristics

Parameter		Test Conditions	V _{CC} = 1.8V Typ.	V _{CC} = 2.5V Typ.	V _{CC} = 3.3V Typ.	V _{CC} = 5V Typ.	Unit
C _{pd}	Power Dissipation Capacitance	f = 10MHz	19	19	20	22	pF

Package Characteristics

Symbol	Parameter	Package	Test Conditions	Min	Тур.	Max	Unit
	θ _{JA} Thermal Resistance Junction- to-Ambient	X2-DFN2010-8		—	313	—	
θ _{JA}		X2-DFN1410-8	(Note 10)	_	321	—	°C/W
		X2-DFN1210-8		_	395	—	
		X2-DFN2010-8		_	145	_	
θ _{JC} Thermal Resistance Junctio	Thermal Resistance Junction- to-Case	X2-DFN1410-8	(Note 10)	_	166	—	°C/W
	10-0458	X2-DFN1210-8		_	236	_]

Note: 10. Test condition for each package type: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Switching Characteristics

Deserved	From To		V	TA	= -40°C to +85	5°C	T _A = -40°C	to +125°C	
Parameter	Input	Output	Vcc	Min	Тур	Max	Min	Мах	Unit
		1.8V ± 0.15V	1.2	3.5	8.6	1.2	10.8		
			2.5V ± 0.2V	0.7	2.3	4.8	0.7	6.0	
t _{pd}	A or B	Y	2.7V	0.7	3.0	5.6	0.7	7.0	ns
			3.3V ± 0.3V	0.7	2.2	4.3	0.7	5.4	
			5.0V ± 0.5V	0.5	1.8	3.3	0.5	4.2	

Typical Values at $T_A = +25^{\circ}$ C and nominal voltages 1.8V, 2.5V, 2.7V, 3.3V, and 5.0V. See Figure 1.



Parameter Measurement Information



V _{cc}	In	puts	V _M	CL	R∟	
V CC	Vı	t _r /t _f	VM CL		ις_	
1.8V ± 0.15V	V _{cc}	≤2ns	V _{CC} /2	30pF	1kΩ	
2.5V ± 0.2V	V _{cc}	≤2ns	V _{CC} /2	30pF	500Ω	
2.7V	2.7V	≤2.5ns	1.5V	50pF	500Ω	
3.3V ± 0.3V	2.7V	≤2.5ns	1.5V	50pF	500Ω	
5.0V ± 0.5V	V _{cc}	≤2.5ns	V _{CC} /2	50pF	500Ω	



Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Figure 1. Load Circuit and Voltage Waveforms

A. Includes test lead and test apparatus capacitance. B. All pulses are supplied at pulse repetition rate \leq 10MHz. Notes:

- C. Inputs are measured separately one transition per measurement.
- D. t_{PLH} and t_{PHL} are the same as t_{pd} .



Marking Information

(Top View)



XX : Identification Code Y : Year : 0~9 W : Week : A~Z : 1~26 week; a~z : 27~52 week; z represents 52 and 53 week

X : Internal Code

Part Number	Package	Identification Code
74LVC2G00HD4-7	X2-DFN2010-8	4T
74LVC2G00HK3-7	X2-DFN1410-8	4U
74LVC2G00RA3-7	X2-DFN1210-8	4V



X2-DFN1210-8 Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



	X2-DFN	1210-8	
Dim	Min	Max	Тур
Α	-	0.35	0.30
A1	0	0.03	0.02
b	0.10	0.20	0.15
D	1.15	1.25	1.20
E	0.95	1.05	1.00
е	-	-	0.30
k	-	-	0.25
k1	-	-	0.20
L	0.25	0.35	0.30
L1	0.30	0.40	0.35
z	0.050	0.100	0.075
z1	0.050	0.100	0.075
All [Dimens	ions in	mm

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



X2-DFN1210-8

Dimensions	Value (in mm)
С	0.300
G	0.150
Х	0.150
X1	1.050
Y	0.500
Y1	1.150



X2-DFN1410-8 Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



X2-DFN1410-8				
Dim	Min	Max	Тур	
Α	0.30	0.35	0.33	
A1	0.00	0.03	0.02	
A3			0.10	
b	0.12	0.20	0.15	
D	1.30	1.40	1.35	
E	0.95	1.05	1.00	
е			0.35	
e1			0.55	
L	0.27	0.35	0.30	
L1	0.32	0.40	0.35	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



X2-DFN1410-8

Dimensions	Value (in mm)
С	0.350
Х	0.200
X1	1.250
Y	0.600
Y1	0.650
Y2	1.400



X2-DFN2010-8 Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN2010-8



X2-DFN2010-8					
Dim	Min	Max	Тур		
Α		0.40			
A1	0.00	0.05	0.02		
A3			0.13		
b	0.20	0.30	0.25		
D	1.950	2.05	2.00		
E	0.95	1.05	1.00		
е			0.50		
L	0.30	0.40	0.35		
Z			0.125		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.500
Х	0.300
X1	1.800
Y	0.600
Y1	1.400

X2-DFN2010-8



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